NPN Triple Diffused Planar Silicon Transistor

2SC5698



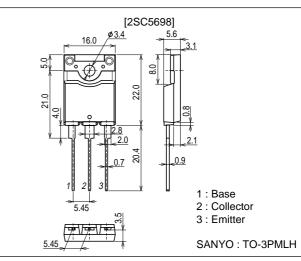
CRT Display Horizontal Deflection Output Applications

Features

- High speed.
- High breakdown voltage(VCBO=1500V).
- High reliability(Adoption of HVP process).
- www.DataSheetAdoption of MBIT process.
 - On-chip damper diode.

Package Dimensions

unit : mm 2174A



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		1500	V
Collector-to-Emitter Voltage	VCEO		800	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		8	А
Collector Current (Pulse)	ICP		16	А
Collector Dissipation	De		3.0	W
	PC	Tc=25°C	65	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =800V, I _E =0			10	μA
Collector Cutoff Current	ICES	VCE=1500V, RBE=0			1.0	mA
Collector Sustain Voltage	VCEO(sus)	I _C =100mA, I _B =0	800			V
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0	40		130	mA
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=4.5A, IB=1.13A			3	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =4.5A, I _B =1.13A			1.5	V

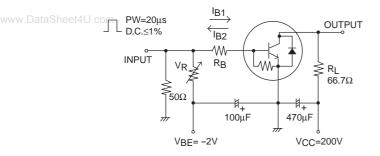
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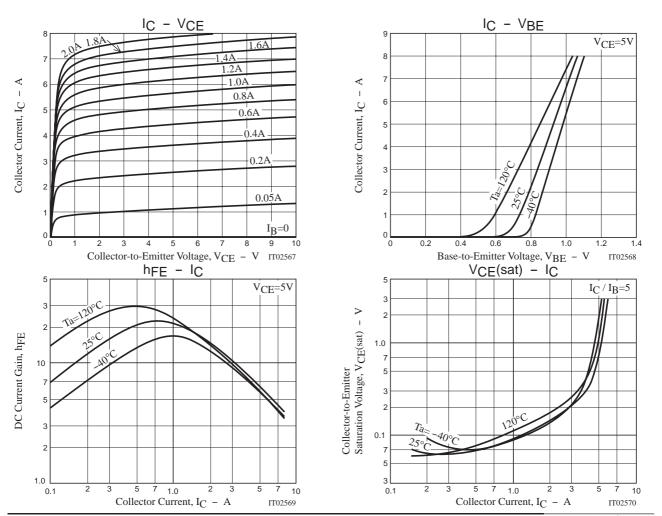
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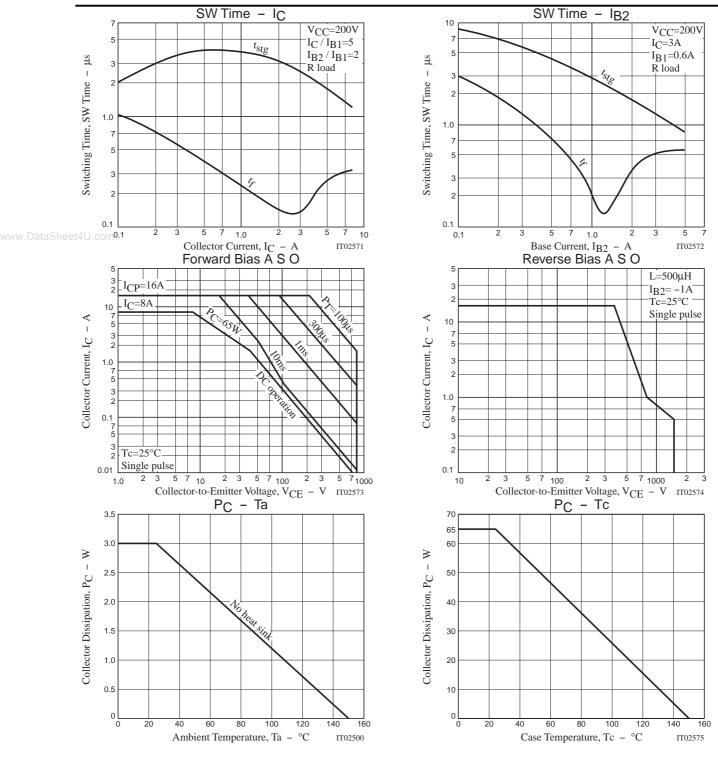
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
DC Current Gain	hFE1	V _{CE} =5V, I _C =1A	5			
	hFE2	V _{CE} =5V, I _C =5A	4		7	
Diode Forward Voltage	VF	IEC=6.5A			2	V
Storage Time	tstg	IC=3A, IB1=0.6A, IB2=-1.2A			3.0	μs
Fall Time	tf	I _C =3A, I _{B1} =0.6A, I _{B2} =-1.2A			0.2	μs

Switching Time Test Circuit





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